

Structural analysis of thin films by reflectometry

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What is (specular) X-ray and neutron reflectometry for thin films ?

Definition : *specular* means that the incident angle equals the reflection angle relative to the surface normal of the thin film.

Key points

- ▶ measure the intensity of the reflected beam as a function of incident angle to deduce the properties of the material
- ▶ it works because there is 'density' contrast → refraction
- ▶ depth profiling → layer thicknesses, roughnesses, and densities (gradients)
- ▶ *in situ* measurements : growth, adsorption, annealing, ...
- ▶ research fields : thin films for semiconductor devices, optical and other coatings, magnetic layers, biological membranes, ...

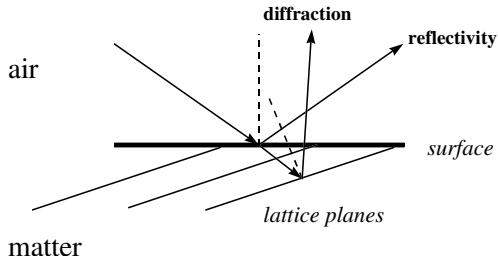
Reflectivity versus diffraction

Diffraction : *interference* induced by long-range order, very often 3D

diffraction plane : fictitious diffraction planes

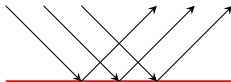
Réflectivité : *interference* by electronic density contrast, always 1D

diffusion plane : surface or physical interface

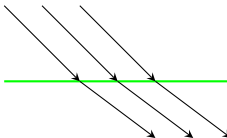


Reflection, refraction and diffraction

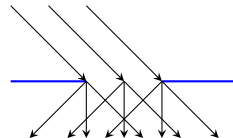
reflection



refraction



diffraction



Personal thoughts

X-ray reflectivity : emphasizes the reflection of X-rays, measured by reflectometry

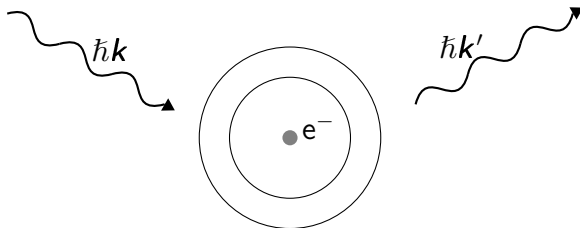
X-ray reflectometry : focusses on the technique to measure the reflectivity

A reflectometry experiment always combines the reflection and refraction of X-rays and may include diffraction (or rather interference) effects.

X-ray reflectivity should actually be called *X-ray refractivity* in view of the importance of refraction at very low angles.

X-ray reflectometry is a **diffusion technique** which permits to determine the **electronic density** across a **stratified medium**

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Units and magnitudes

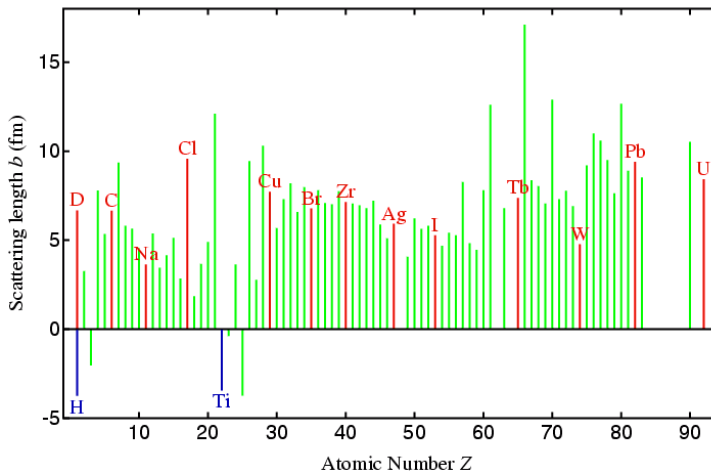
$$A_{\text{sc}} = -A_{\text{in}} b \frac{e^{-ikr}}{r}$$

- ▶ b is the **scattering power** or **scattering length** ; it is expressed in length units.
 - ▶ electron : $b = r_0$ Thomson scattering length ($= 2.82 \cdot 10^{-5}$ Å)
 - ▶ nucleus : $b = b_c$ coherent scattering length

For a multi-element compound a scattering length density (SLD ou ρ) is defined by :

$$\rho = \frac{\sum_{i=1}^N b_i}{V_m} = \frac{\sum_{i=1}^N Z_i r_0}{V_m}$$

Coherent scattering length (neutrons)



Units and magnitudes

The scattering length density is expressed in $[\text{area}]^{-2}$ and can be linked to the electronic density ρ_e and mass density ρ_m by :

$$\rho = r_0 \rho_e$$

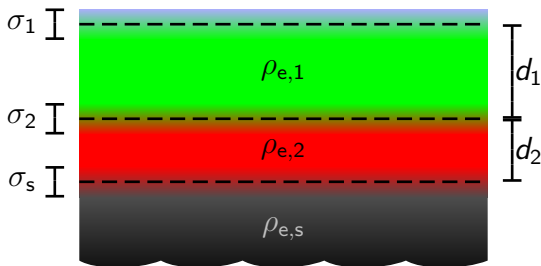
and

$$\rho = N_A r_0 \rho_m \frac{\sum c_i Z_i}{\sum c_i A_i}$$

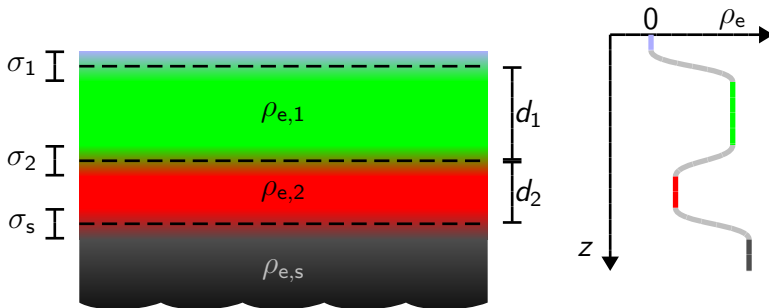
The goal of a reflectometry experiment is to determine ρ (or ρ_e or ρ_m).

X-ray reflectometry is a **diffusion technique** which permits to determine the **electronic density** across a **stratified medium**

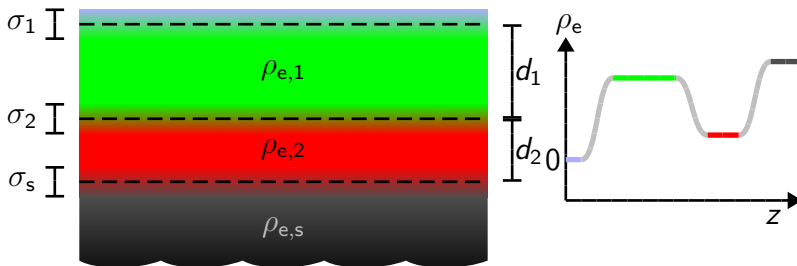
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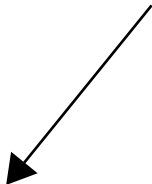
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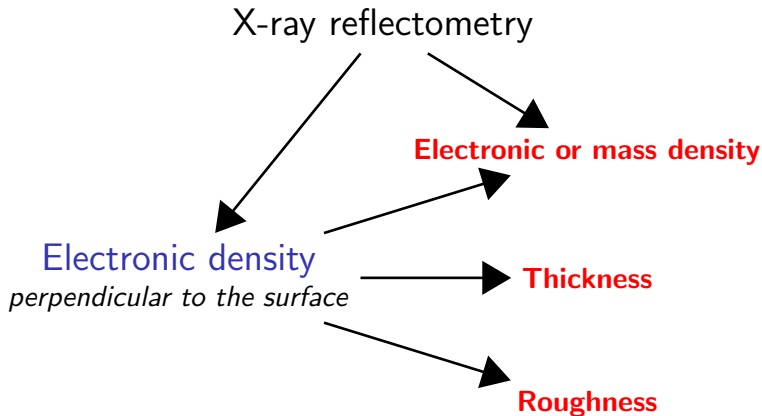


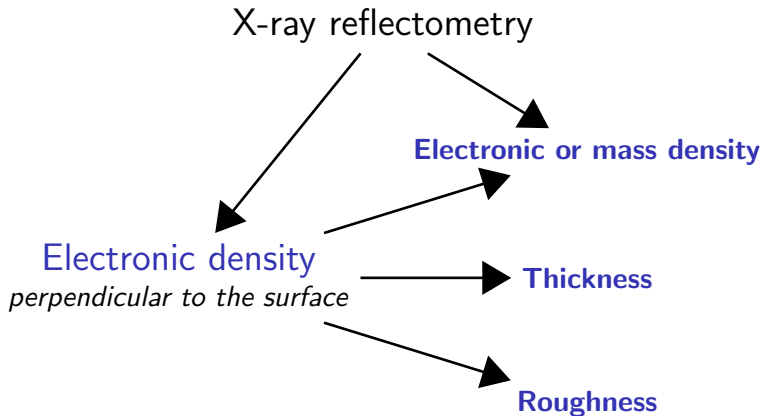
X-ray reflectometry



Electronic density

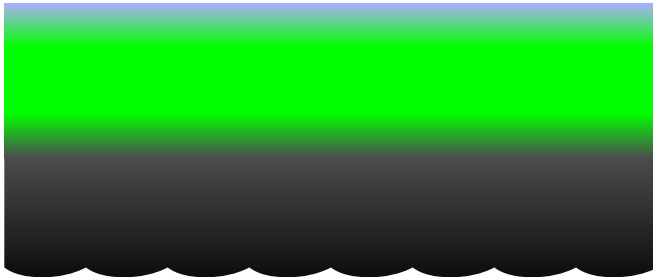
perpendicular to the surface

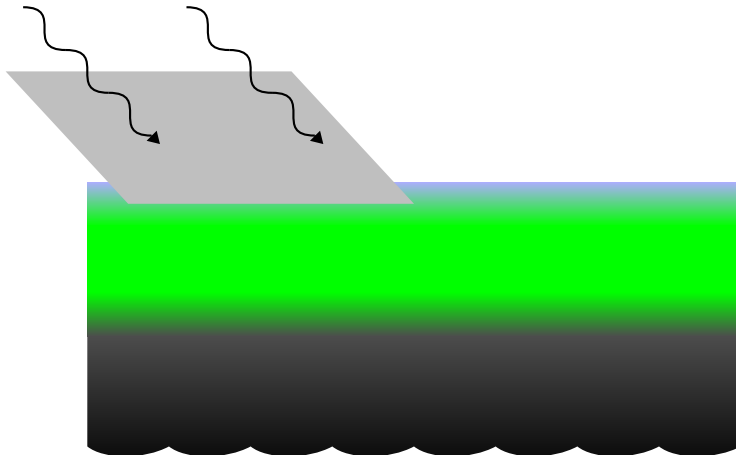


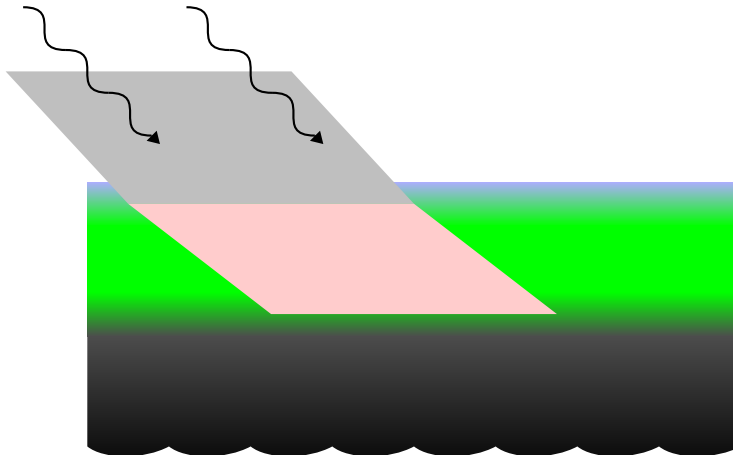


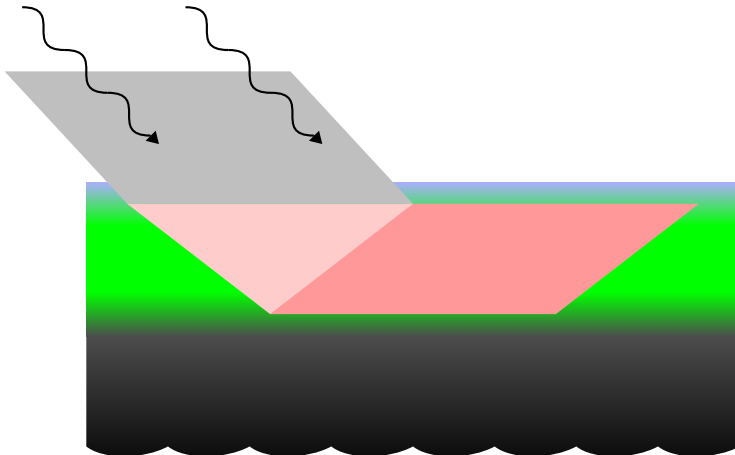
Maximum 3 layers

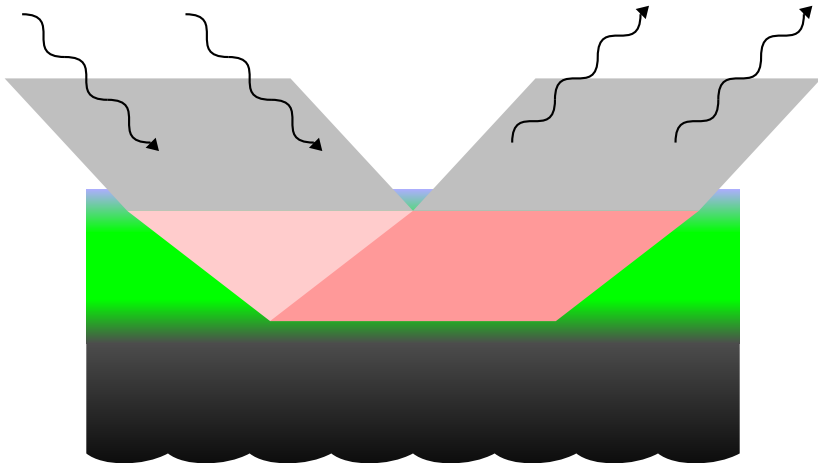
- └ Interaction of X-rays with interfaces and thin films
- └ Snell-Descartes and Bragg

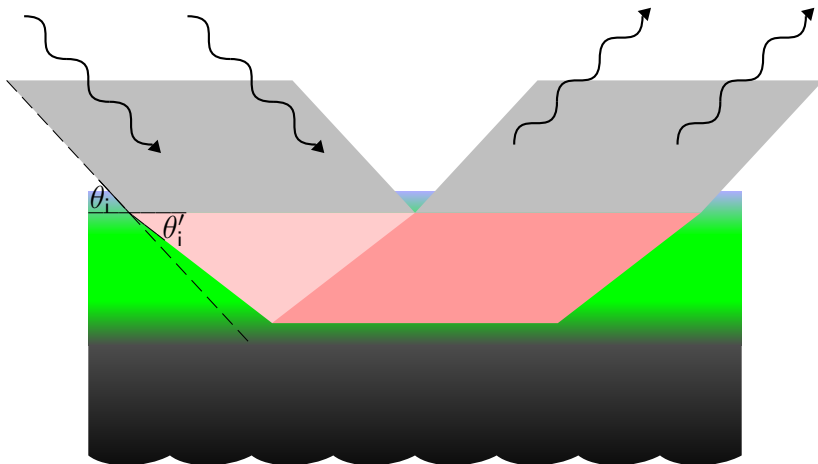




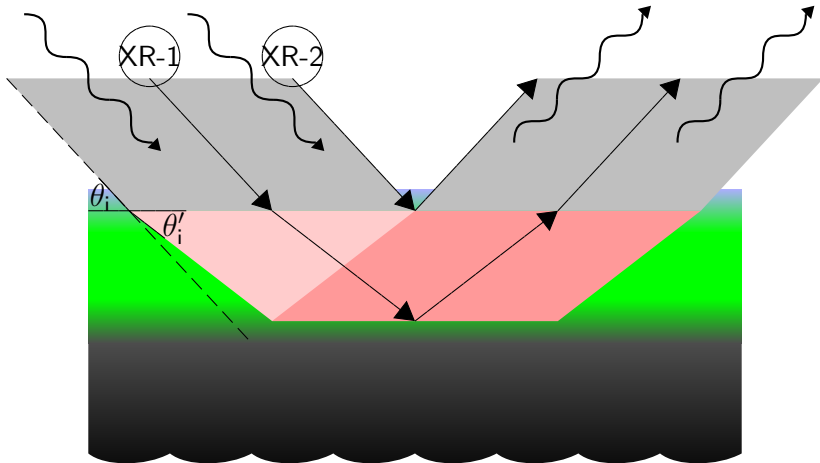




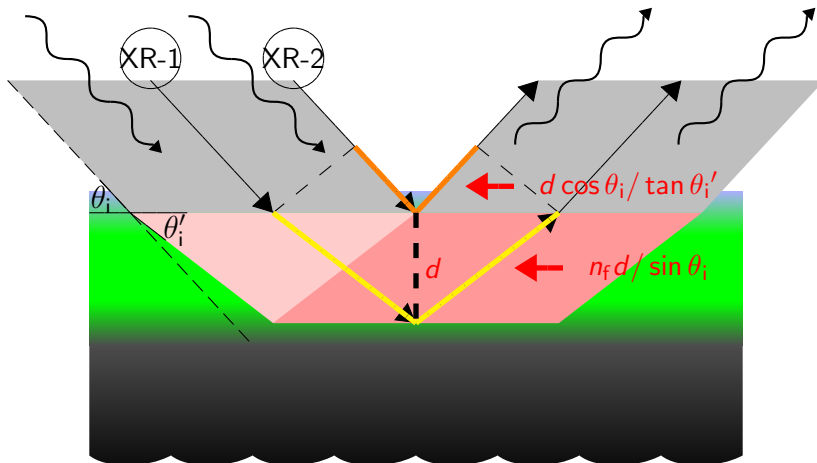




Loi de Snell-Descartes : $\cos \theta_i = n_f \cos \theta_i'$



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Calculation of the refracted angle

$$\cos \theta_i = n_f \cos \theta_i'$$

$$\cos \theta_i' = \frac{\cos \theta_i}{n_f}$$

$$n_f = 1.0 - \frac{r_0 \lambda^2}{4\pi^2} \rho_e$$

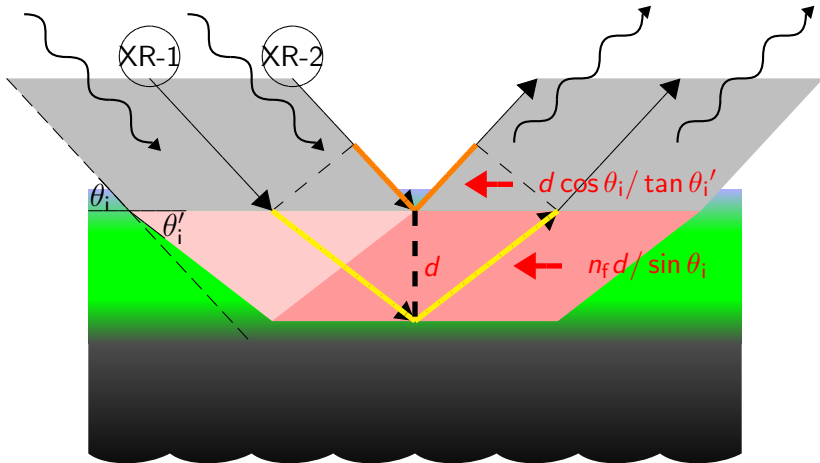
$\cos \theta_i' > 1.00$ if θ_i very small ...

$$\cos \theta_c = n_f = 1.0 - \frac{r_0 \lambda^2}{4\pi^2} \rho_e$$

Some critical angles ($\lambda = 1.5405\text{\AA}$)

compound	Mass density (gcm^{-3})	electronic density ($\text{e}\text{\AA}^{-3}$)	critical angle ($^{\circ}$)
Si	2.333	0.701	0.224
Al_2O_3	3.998	1.181	0.287
Ge	5.893	1.588	0.333
ZnO	5.653	1.589	0.334
InN	6.921	1.811	0.356
Au	19.283	4.656	0.571

- Interaction of X-rays with interfaces and thin films
- Critical angle and electronic density



$$\text{Snell-Descartes law : } \cos \theta_i = n_f \cos \theta_i'$$

In order to have constructive interference the difference in optical path lengths should be :

$$m\lambda = 2d \left(\frac{n_f}{\sin \theta'} - \frac{\cos \theta}{\tan \theta'} \right)$$

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$$\sin^2 \theta = \frac{m^2 \lambda^2}{4d^2} + \sin^2 \theta_c = \frac{m^2 \lambda^2}{4d^2} + \frac{\lambda^2 r_0 \rho_e}{\pi}$$

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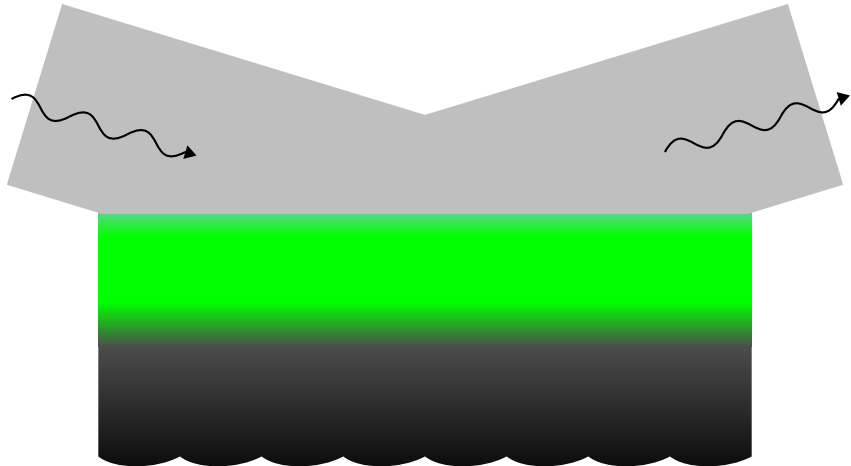
$$\sin^2 \theta = \frac{m^2 \lambda^2}{4d^2} + \cancel{\sin^2 \theta_c} = \frac{m^2 \lambda^2}{4d^2} + \cancel{\frac{\lambda^2 r_0 \rho_e}{\pi}} \Rightarrow \sin \theta = \frac{m\lambda}{2d} \Rightarrow \boxed{m\lambda = 2d \sin \theta}$$

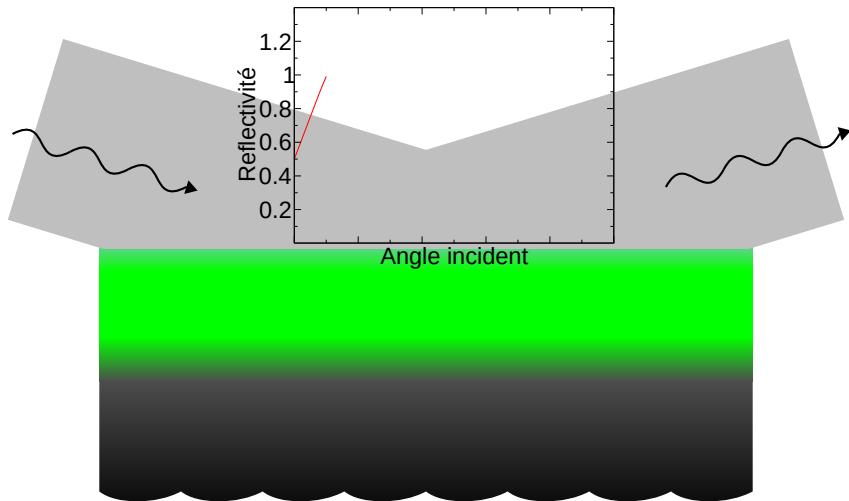
$$\Phi_i = N_0$$

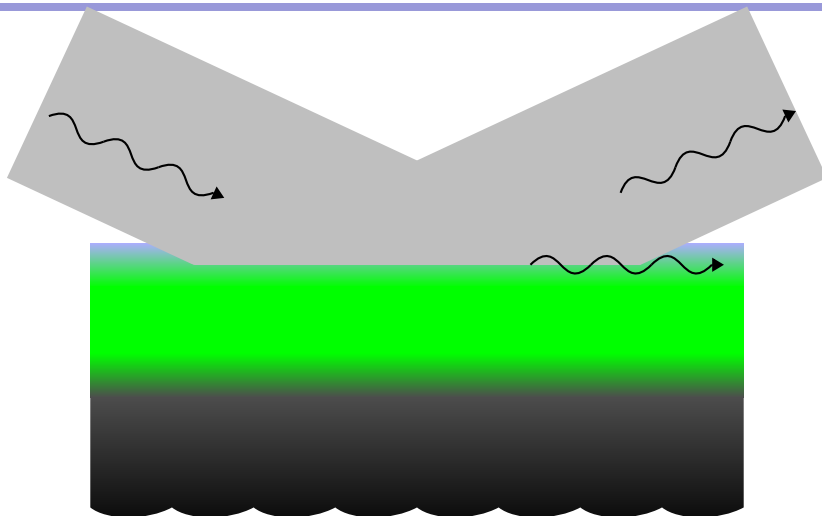
$$R = \frac{\Phi_i}{\Phi_e} = \frac{1}{2}$$

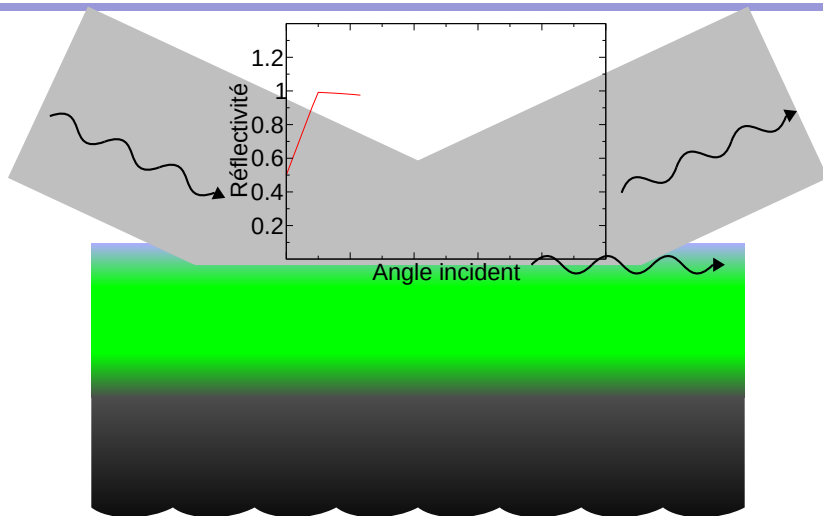
$$\Phi_e = N_0/2$$

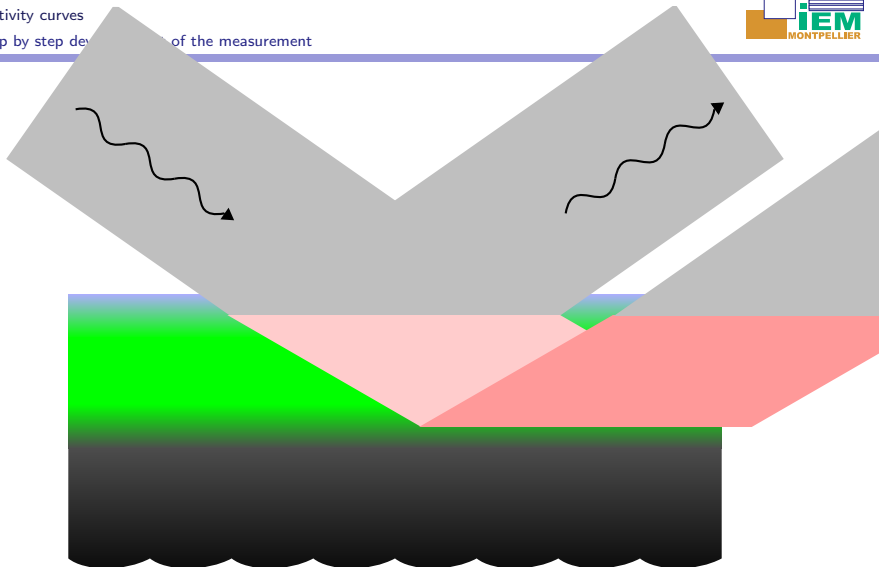


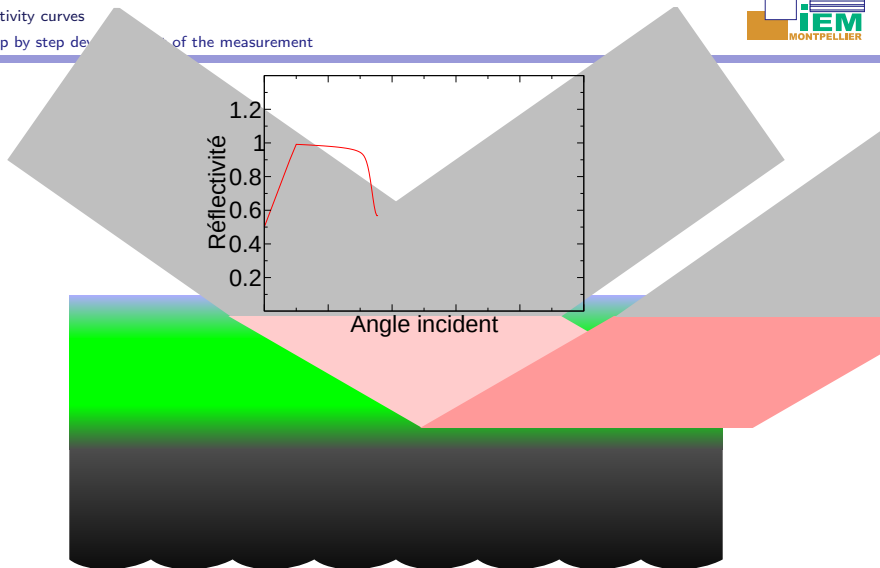


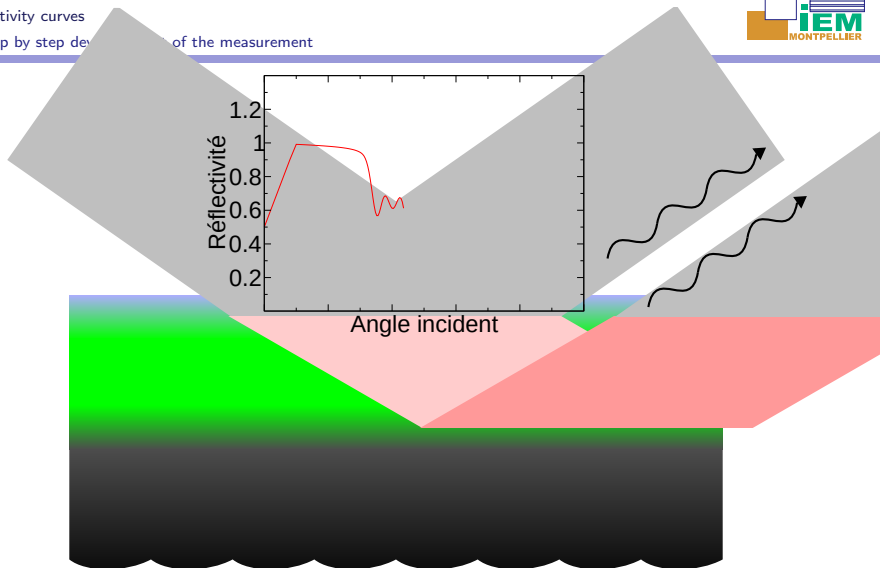


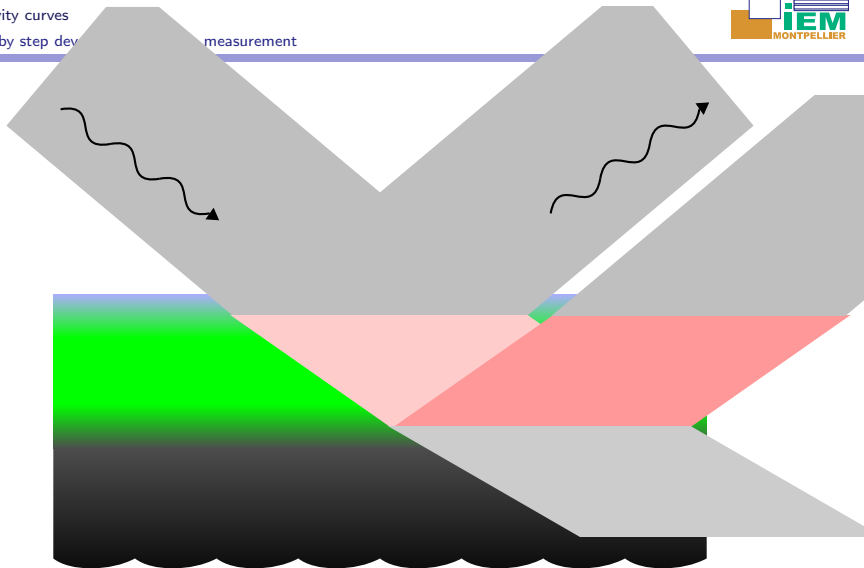


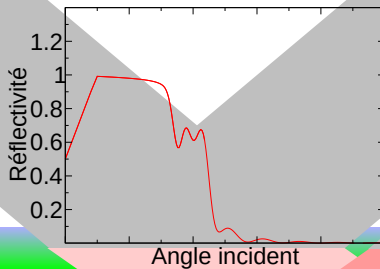




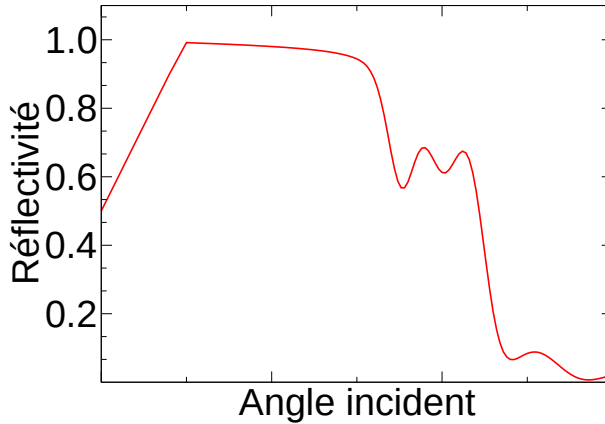


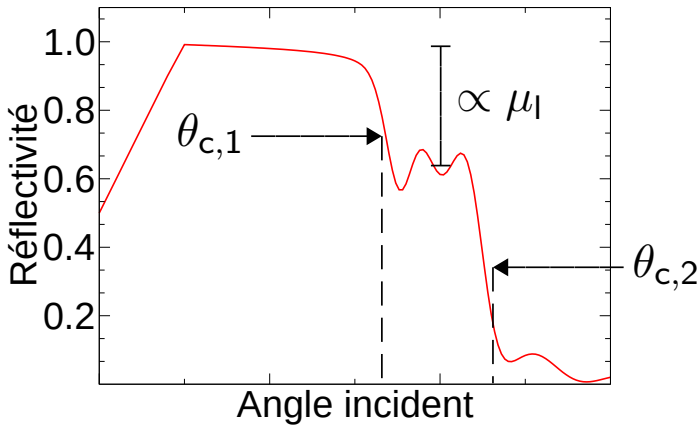


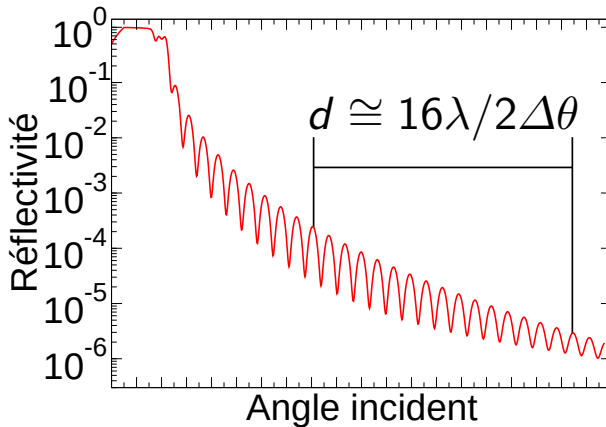


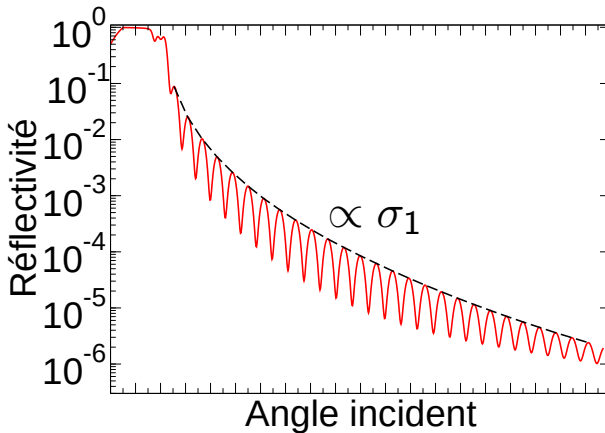


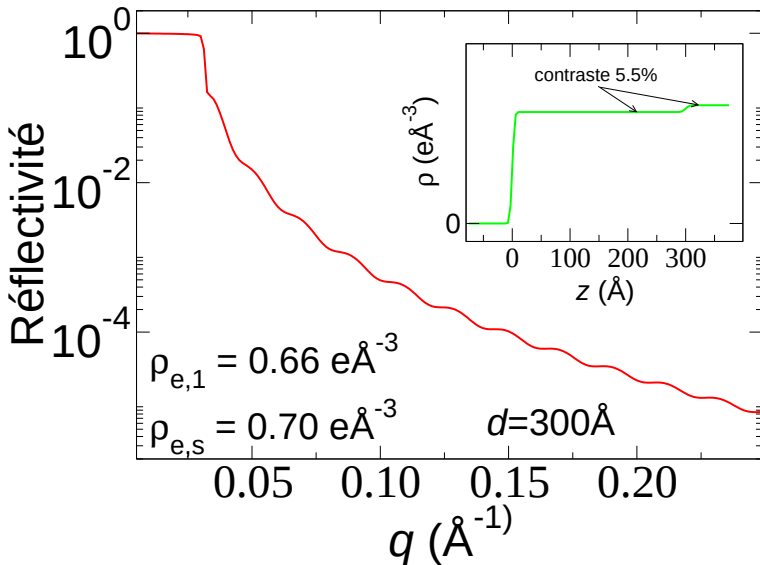


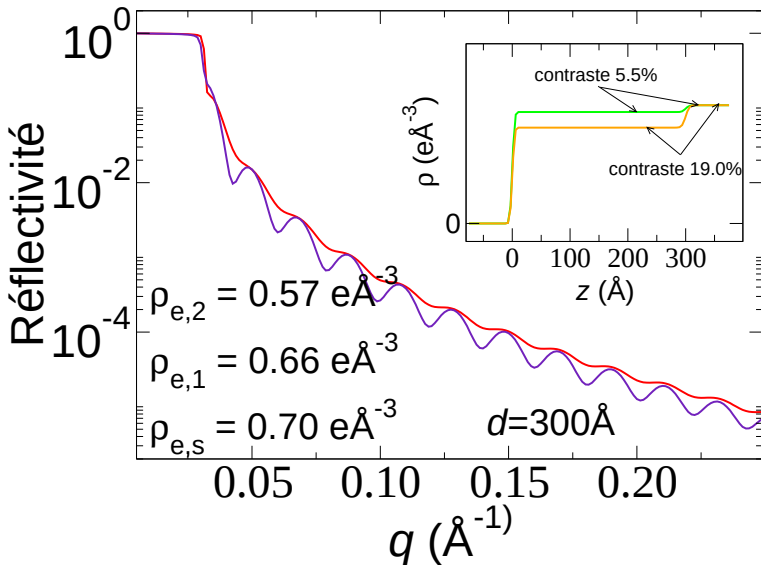


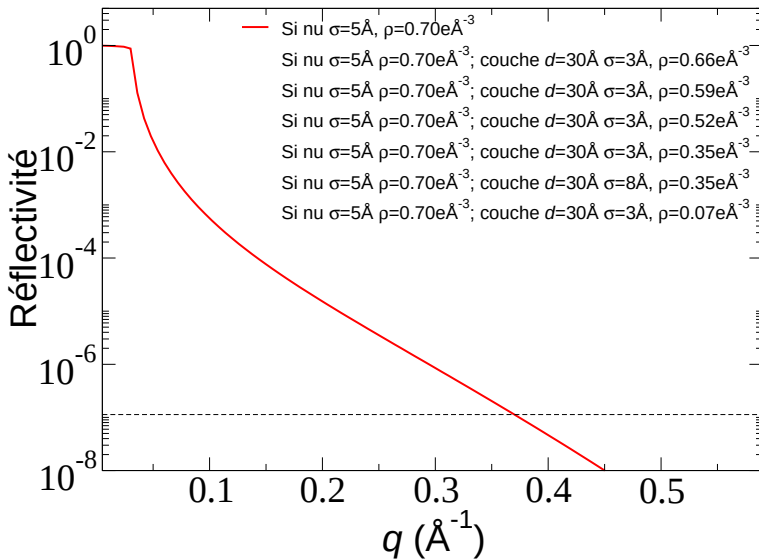


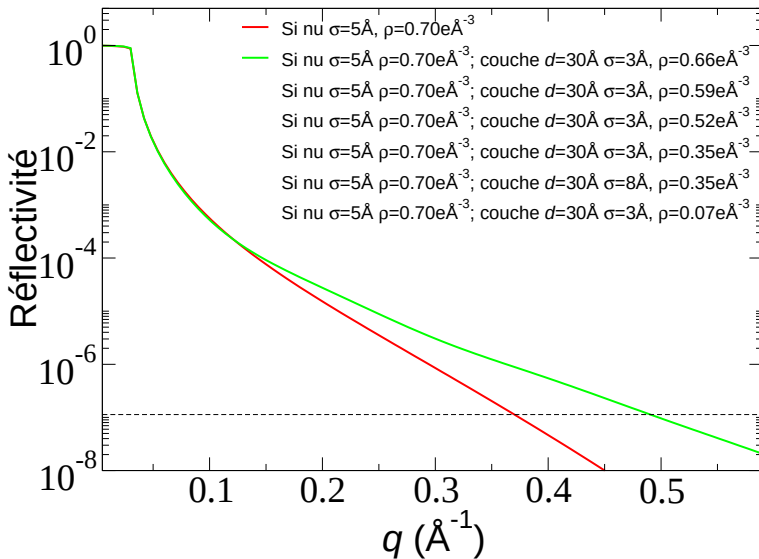


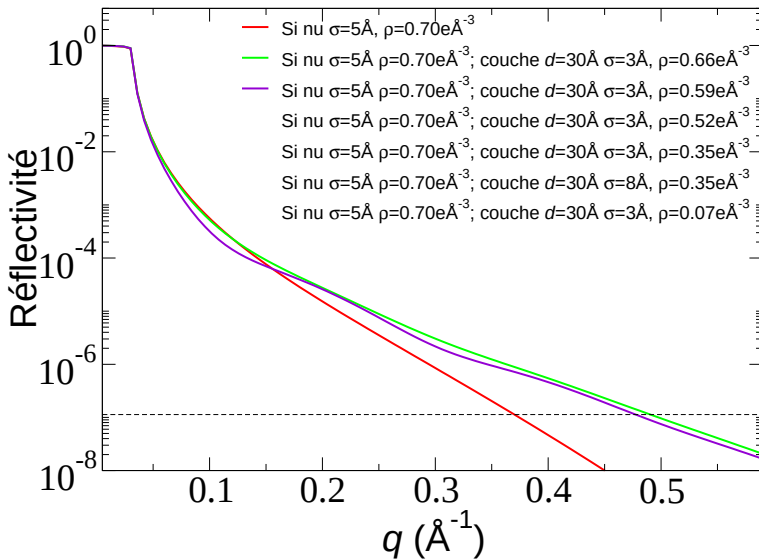


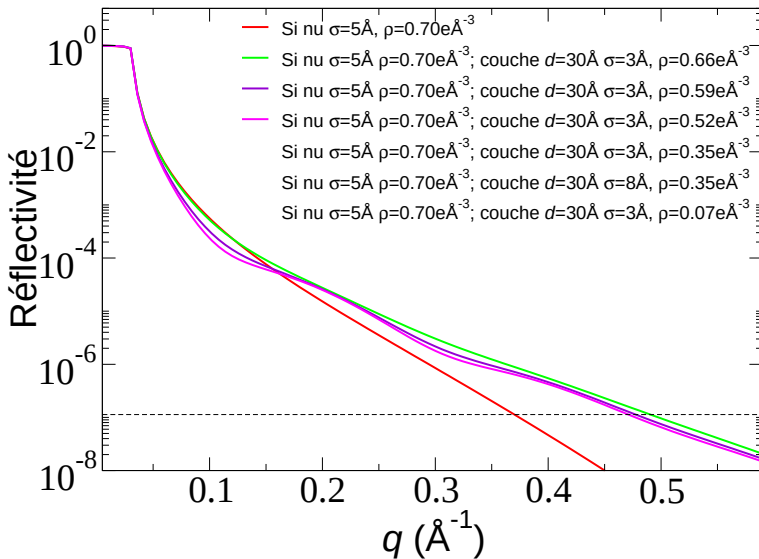


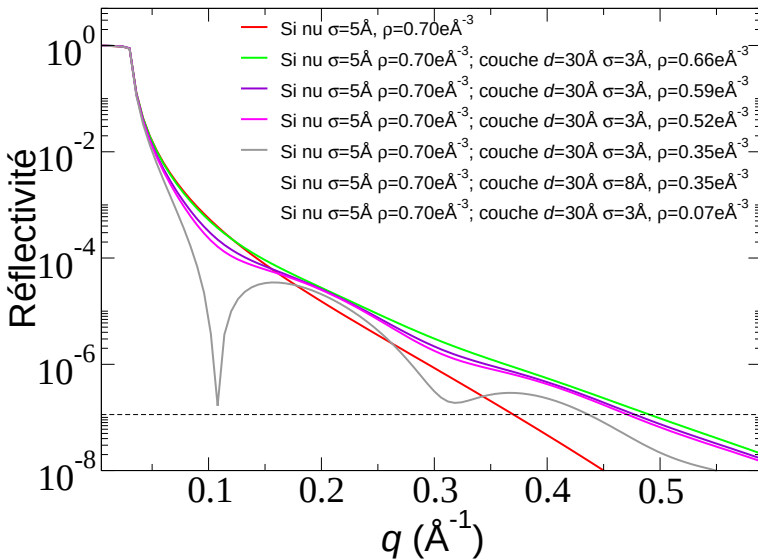


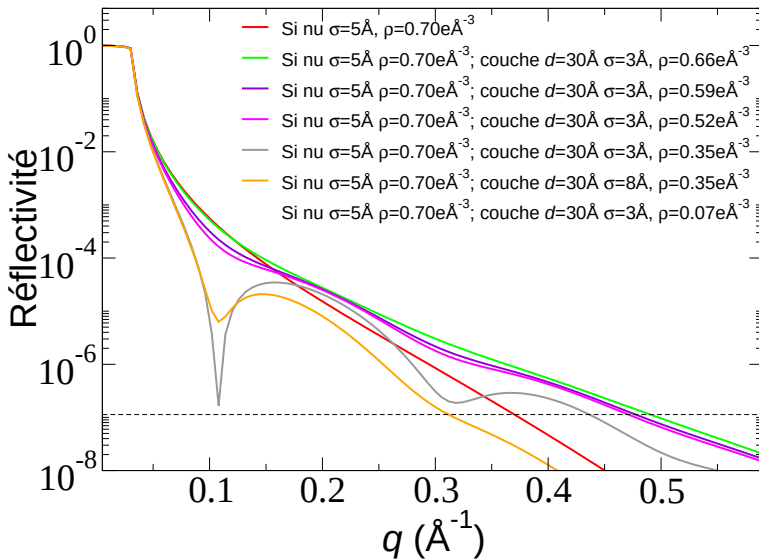


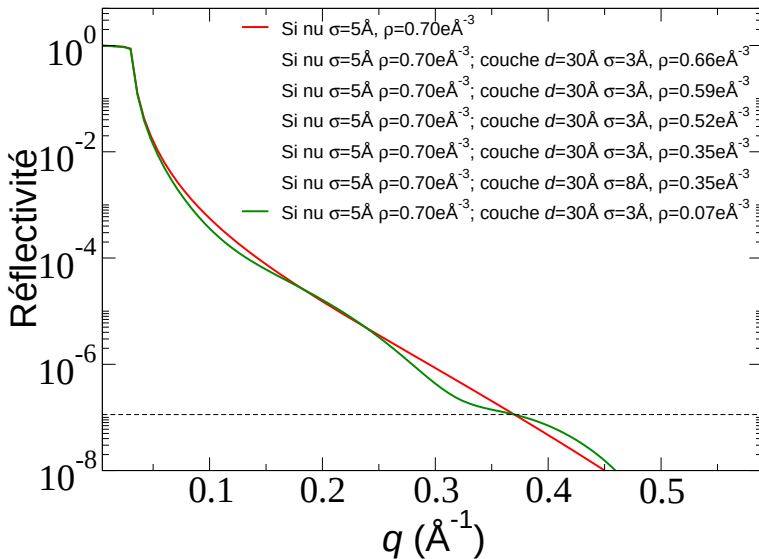


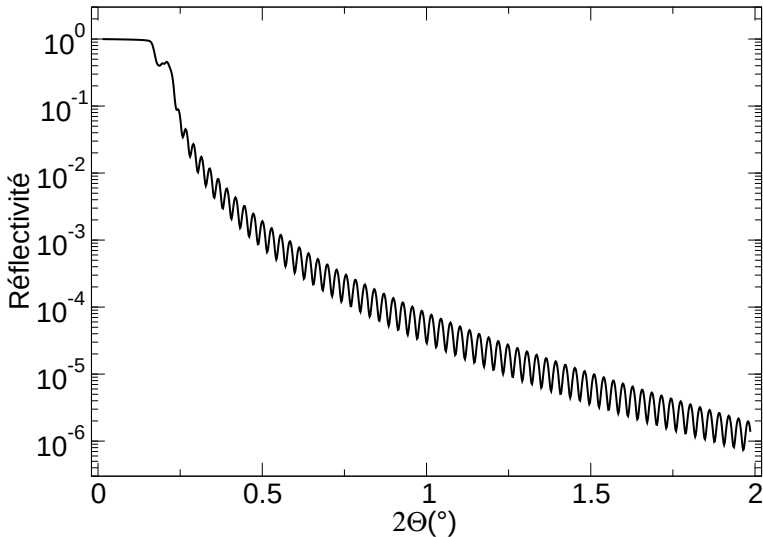


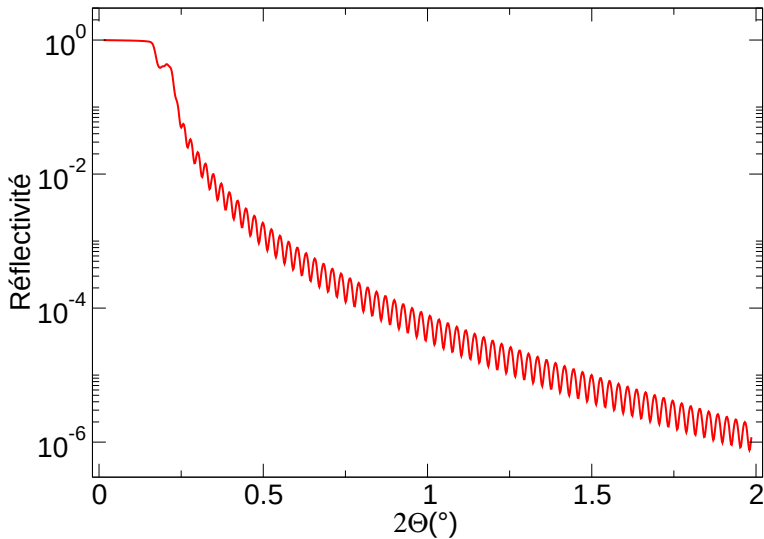


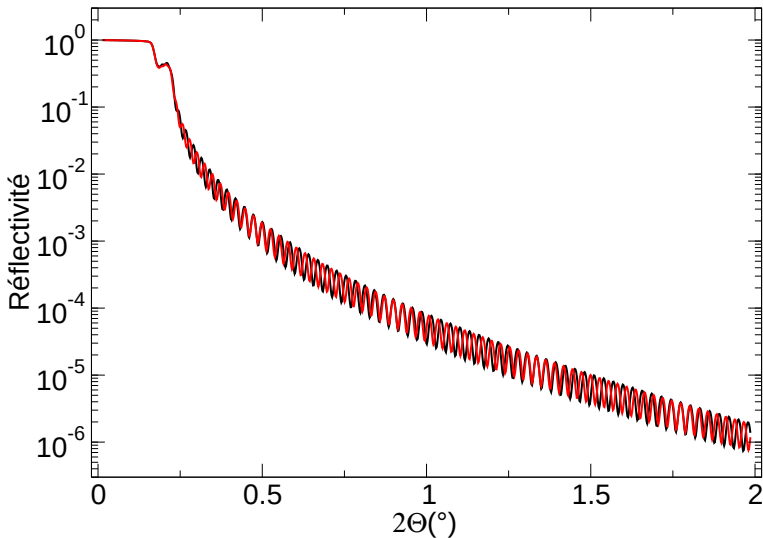


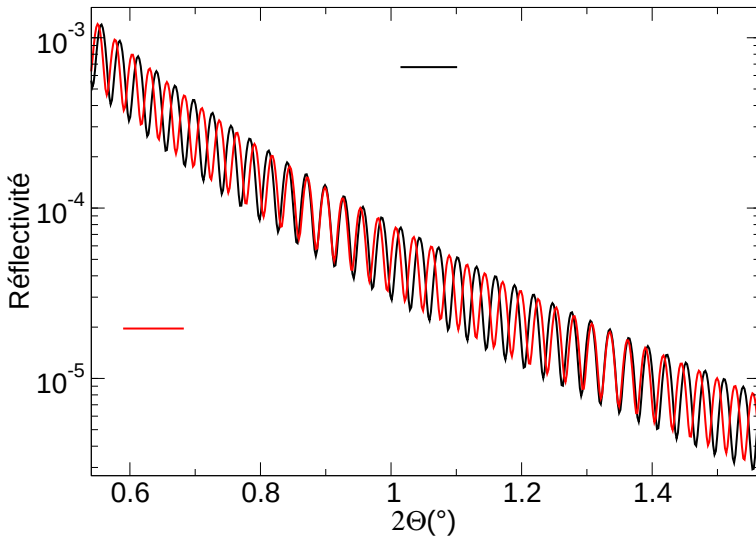


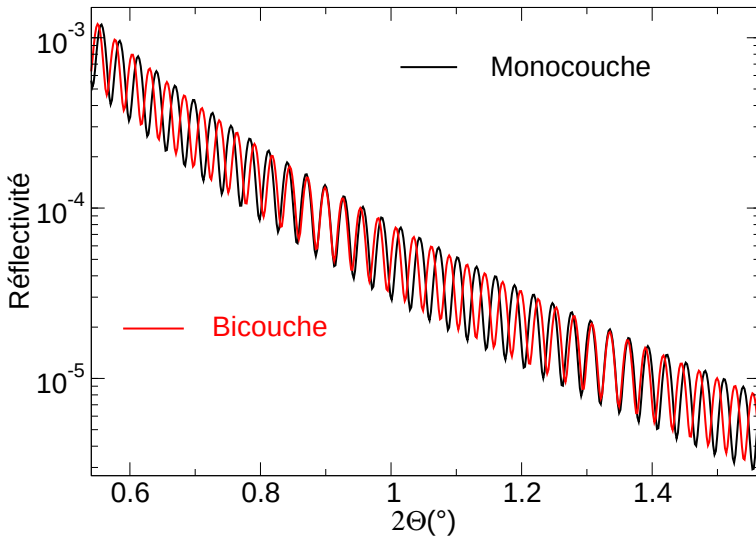




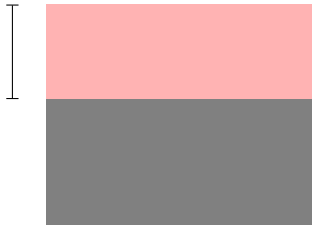








150 nm



10 nm



Single layer

- ▶ $\rho_m = 1.36 \text{ gcm}^{-3}$
- ▶ $d = 150 \text{ nm}$
- ▶ $\sigma_1 = 0.5 \text{ nm}$; $\sigma_2 = 0.3 \text{ nm}$
- ▶ substrat silicium

Bilayer

- ▶ $\rho_{m,1} = 1.36 \text{ gcm}^{-3}$; $\rho_{m,2} = 1.80 \text{ gcm}^{-3}$
- ▶ $d_1 = 150 \text{ nm}$; $d_2 = 10 \text{ nm}$
- ▶ $\sigma_1 = 0.5 \text{ nm}$; $\sigma_2 = 0.4 \text{ nm}$; $\sigma_3 = 0.3 \text{ nm}$
- ▶ Silicon substrate

- ▶ Sample size : 20 mm x 20 mm
- ▶ Sample should be 'flat' on a macroscopic scale
- ▶ A lab diffractometer with point detector is usually sufficient
- ▶ Multi-interval measurement with variable step and counting time recommended
- ▶ Thin films need not to be crystalline
- ▶ Time of the measurement : $5 \text{ min} < t_{\text{measurement}} < 24\text{h}$
- ▶ Analysis time : $5 \text{ min} < t_{\text{analysis}} < 1 \text{ week}$

- ▶ thickness between 2 and 450 nm
- ▶ density contrast larger than 3%
- ▶ roughness lower than 4 nm
- ▶ layer should be 'homogeneous'
- ▶ difficult (but not impossible) to make difference between 'interdiffusion' and 'true roughness'

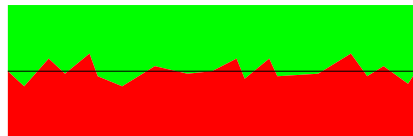


Interdiffusion

- ▶ thickness between 2 and 450 nm
- ▶ density contrast larger than 3%
- ▶ roughness lower than 4 nm
- ▶ layer should be 'homogeneous'
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Interdiffusion

 $\sigma \quad \sigma$ 

RMS roughness

- └ Some experimental considerations
- └ A practical formula

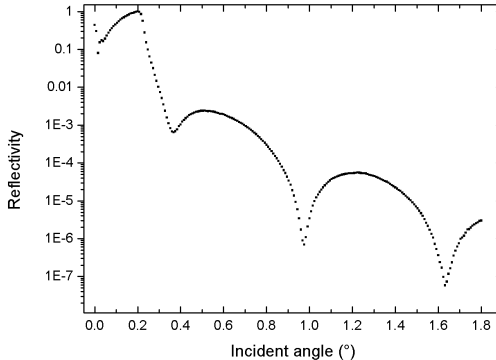
$$\rho_e = N_A \rho_m \frac{\sum c_j Z_j}{\sum c_j A_j}$$

$$\rho_e = N_A \rho_m \frac{\sum c_j Z_j}{\sum c_j A_j}$$

Pour $2 < Z < 18 \Rightarrow A_j \approx 2Z_j$
et par conséquent :

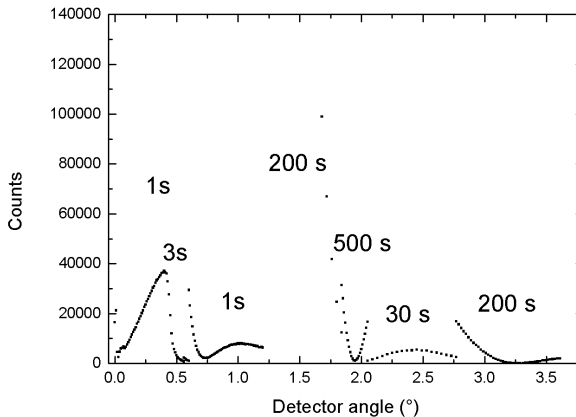
$$\frac{2\rho_e}{N_A} \approx \rho_m$$

A typical measurement of an organic layer of 68 Å



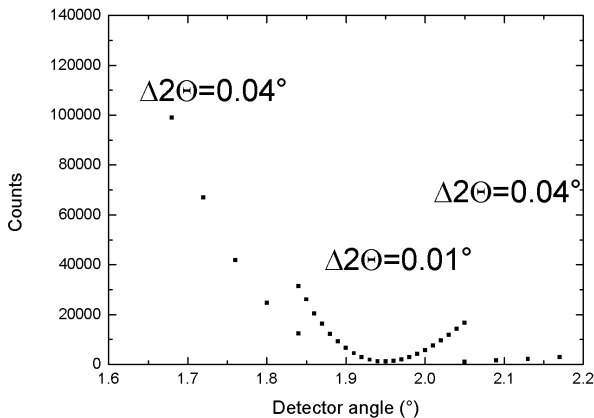
It concerns a measurement for which the data are 'reduced'

Raw data of the preceding curve



Counting time for the different intervals

Raw data of the preceding curve



Differents steps for different intervals

Some basic rules

Because of its large dynamic intensity range (6-7 orders of magnitude) a reflectometry measurement is often multi-interval. For each interval one defines a counting time and optimal step size.

Step size and counting time - I

- ▶ steps
 - ▶ determine the width Δ of a typical fringe
 - ▶ the optimal step size is given by $\Delta(2\theta) \approx \Delta/10$
 - ▶ you could take a smaller step size around the critical angle and close to the minima of very large fringes

Some basic rules

Because of its large dynamic intensity range (6-7 orders of magnitude) a reflectometry measurement is often multi-interval. For each interval one defines a counting time and optimal step size.

Step size and counting time - II

- ▶ counting time
 - ▶ standard deviation of the counting of N photons (Poisson statistics) : $\sqrt{N}$
 - ▶ relative error σ for 1000 photons : $\frac{\sqrt{N}}{N} \approx 0.03$
 - ▶ for each measurement point > 1000 counts $\rightarrow \sigma < 0.03$ everywhere
 - ▶ example (pre-measurement) : $I(2\theta) = 50$ cps
 $\rightarrow T = 20$ s